

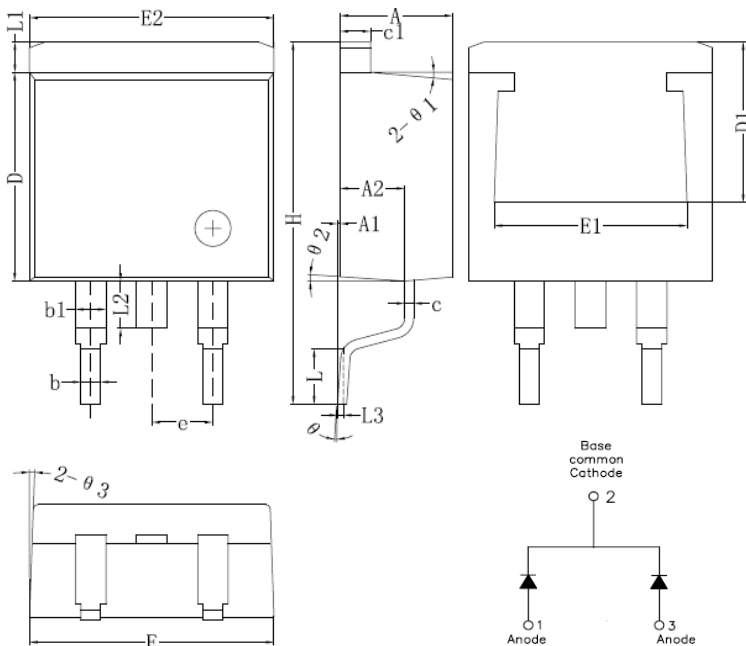
## STB30H100C SCHOTTKY RECTIFIER

**Applications:**

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Center tap configuration

**Features:**

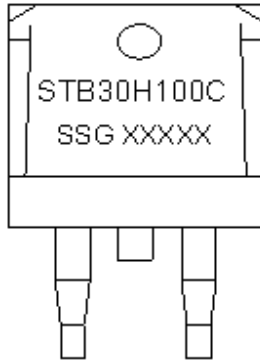
- 175°C T<sub>J</sub> operation
- Center tap configuration
- Ultralow forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Trench MOS Schottky technology
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot

**Mechanical Dimensions: In mm**


Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	4.55	4.70	4.85
A1	0	0.10	0.25
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1		1.27	
c	0.36	0.38	0.61
c1	1.17	1.27	1.37
D	8.55	8.70	8.85
D1	6.40		
E	10.01	10.16	10.31
E1	7.6		
E2	9.98	10.08	10.18
e		2.54	
H	14.6	15.1	15.6
L	2.00	2.30	2.70
L1	1.17	1.27	1.40
L2			2.20
L3		0.25BSC	
e	0	-	8°
e1		5°	
e2		4°	
e3		4°	

### D<sup>2</sup>PAK

**Marking Diagram:**



Where XXXXX is YYWWL

- ST = Device Type
- B = Package type
- 30 = Forward Current (30A)
- H = Tj 175°C
- 100 = Reverse Voltage (100V)
- C = Configuration
- SSG = SSG
- YY = Year
- WW = Week
- L = Lot Number

**Cautions:** Molding resin  
Epoxy resin UL:94V-0

**Ordering Information:**

Device	Package	Shipping
STB30H100C	D <sup>2</sup> PAK (Pb-Free)	800pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

**Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	-	100	V
Average Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_C=100^\circ\text{C}$ , rectangular wave form	30	A
Peak One Cycle Non-Repetitive Surge Current(per leg)	$I_{FSM}$	8.3 ms, half Sine pulse	200	A



# STB30H100C

Technical Data  
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## Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop (per leg)*	V <sub>F1</sub>	@ 7.5A, Pulse, T <sub>J</sub> = 25 °C	0.54	-	V
		@ 15A, Pulse, T <sub>J</sub> = 25 °C	0.76	0.80	
	V <sub>F2</sub>	@ 7.5A, Pulse, T <sub>J</sub> = 125 °C	0.63	-	V
		@ 15A, Pulse, T <sub>J</sub> = 125 °C	0.66	0.70	
Reverse Current at DC Condition (per leg)*	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> T <sub>J</sub> = 25°C	0.005	1	mA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> T <sub>J</sub> = 125°C	1.6	12	mA

\* Pulse Width < 300µs, Duty Cycle <2%

## Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T <sub>J</sub>	-	-55 to +175	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case(per leg)	R <sub>θJC</sub>	DC operation	2.5	°C/W
Approximate Weight	wt	-	1.85	g
Case Style	D <sup>2</sup> PAK			

Figure 1  
Typical Forward Characteristics

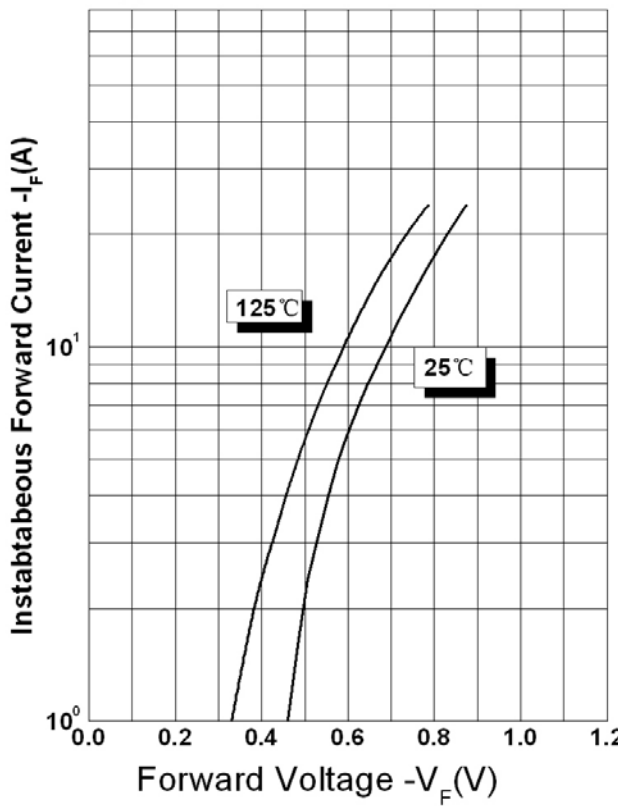


Figure 2  
Typical Reverse Characteristics

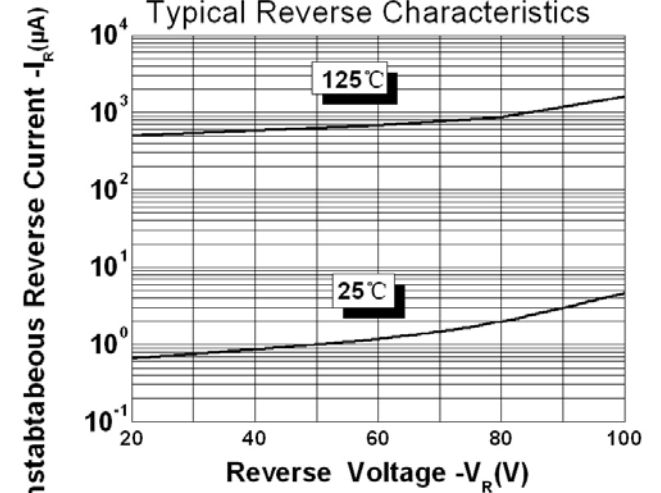
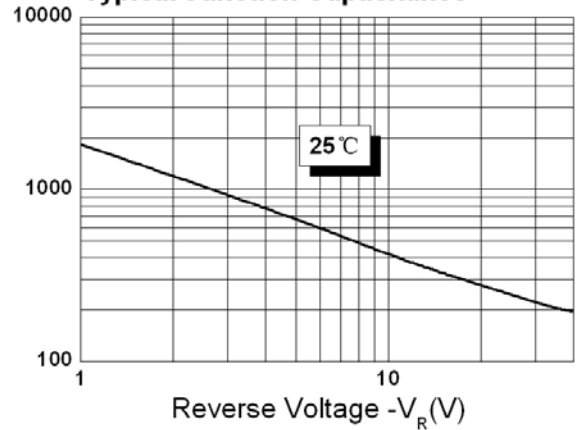


Figure 3  
Typical Junction Capacitance





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